Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

2SC2655

Power Amplifier Applications
Power Switching Applications

- Low saturation voltage: $V_{CE (sat)} = 0.5 \text{ V (max) (IC} = 1 \text{ A)}$
- High collector power dissipation: $P_C = 900 \text{ mW}$
- High-speed switching: $t_{stg} = 1.0 \mu s$ (typ.)
- Complementary to 2SA1020.

Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	50	V	
Collector-emitter voltage	V _{CEO}	50	V	
Emitter-base voltage	V _{EBO}	5	V	
Collector current	IC	2	Α	
Base current	ΙΒ	0.5	Α	
Collector power dissipation	PC	900	mW	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	−55 to 150	°C	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in

0.75MAX. 1.0MAX. 0.8MAX. 0.6MAX. 1.27 1.27 1.27 1.27 1.27 1.27 1.27 1.27 1.27 1.27 1.3 XVWY. 2.54 2.54 3.54

TO-92MOD

2-5J1A

Industrial Applications

Weight: 0.36 g (typ.)

JEDEC

JEITA TOSHIBA

temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

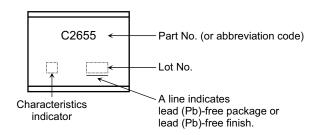


Electrical Characteristics (Ta = 25°C)

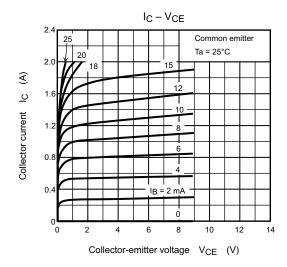
Chara	acteristics Symbol Test Condition		Min	Тур.	Max	Unit	
Collector cut-off c	urrent	I _{CBO}	V _{CB} = 50 V, I _E = 0	_	_	1.0	μΑ
Emitter cut-off cui	rrent	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	1.0	μA
Collector-emitter	breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	50	_	_	V
DC current gain		h _{FE (1)} (Note)	V _{CE} = 2 V, I _C = 0.5 A	70	_	240	
		h _{FE} (2)	V _{CE} = 2 V, I _C = 1.5 A	40	_	_	
Collector-emitter	saturation voltage	V _{CE} (sat)	I _C = 1 A, I _B = 0.05 A	_	_	0.5	V
Base-emitter satu	ration voltage	V _{BE} (sat)	I _C = 1 A, I _B = 0.05 A	_	_	1.2	V
Transition frequer	ncy	f _T	V _{CE} = 2 V, I _C = 0.5 A	_	100	_	MHz
Collector output capacitance		C _{ob}	V _{CB} = 10 V, I _C = 0, f = 1 MHz	_	30	_	pF
Switching time Storag	Turn-on time	t _{on}	20 μs Input B1	_	0.1	_	
	Storage time	t _{stg}	Input $\stackrel{\text{IB}}{\longrightarrow}$ $\stackrel{\text{Cl}}{\longrightarrow}$ $\stackrel{\text{Cl}}$	_	1.0	_	μs
	Fall time	t _f		_	0.1	_	

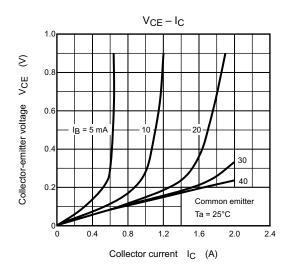
Note: hFE (1) classification O: 70 to 140, Y: 120 to 240

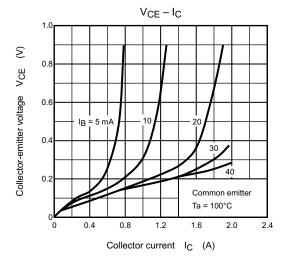
Marking

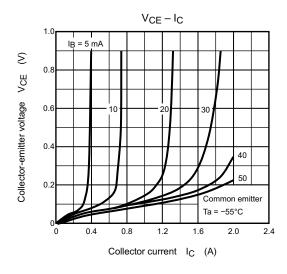


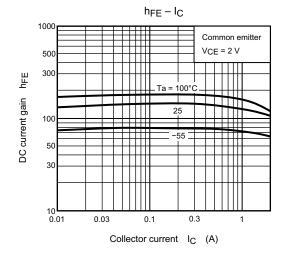
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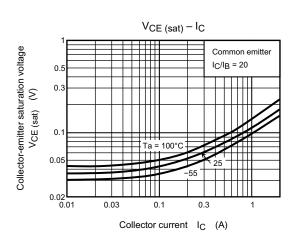


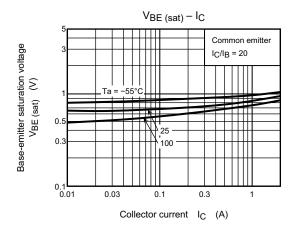


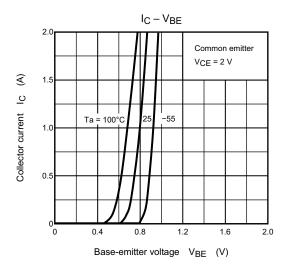


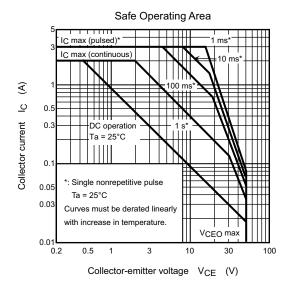


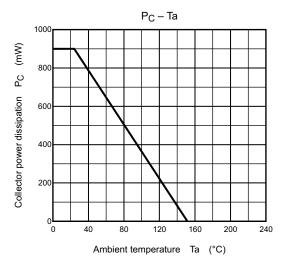












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